



Dual P-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | |
|---------------------|---|--------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}\left(\Omega\right)$ | I _D (A) | | |
| - 30 | $0.133 \text{ at V}_{GS} = -10 \text{ V}$ | - 2.2 | | |
| | 0.245 at V _{GS} = - 4.5 V | - 1.6 | | |

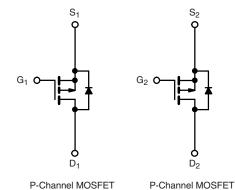
FEATURES

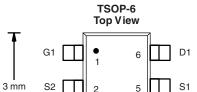
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Symetrical Dual P-Channel
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Battery Switch for Portable Devices
- Computers
 - Bus Switch
 - Load Switch







Ordering Information: Si3993DV-T1-E3 (Lead (Pb)-free) Si3993DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

D2

Marking Code:

G2

| ABSOLUTE MAXIMUM RATINGS | T _A = 25 °C, unles | ss otherwise r | noted | | |
|---|-------------------------------|-----------------------------------|-------------|--------------|------|
| Parameter | | Symbol | 5 s | Steady State | Unit |
| Drain-Source Voltage | | V _{DS} | - 30 | | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | | V |
| 0 D 0 (T 150.00)8 | T _A = 25 °C | I _D | - 2.2 | - 1.8 | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 70 °C | | - 1.7 | - 1.4 | |
| Pulsed Drain Current | | I _{DM} | - 8 | | Α |
| Continuous Source Current (Diode Conduction) ^a | | I _S | - 1.05 | - 0.75 | |
| M | T _A = 25 °C | В | 1.15 | 0.83 | W |
| Maximum Power Dissipation ^a | T _A = 70 °C | - P _D | 0.73 | 0.53 | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | °C |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Manianum lumation to Ambient | t ≤ 5 s | R _{thJA} | 93 | 110 | °C/W | |
| Maximum Junction-to-Ambient ^a | Steady State | ithJA | 130 | 150 | | |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 75 | 90 | | |

a. Surface Mounted on 1" x 1" FR4 board.

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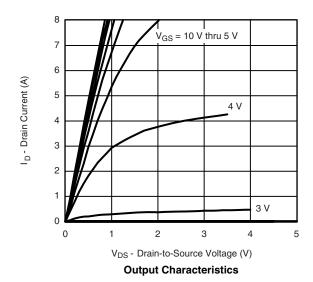
| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | | |
|--|---------------------|---|------|--------|--------|------|--|
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
| Static | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | - 1 | | - 3 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| Zoro Cata Valtago Drain Current | | V _{DS} = - 30 V, V _{GS} = 0 V | -1 | | - 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$ | | | - 5 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$ | - 5 | | | Α | |
| Durin Course Co Olata Basistana a | B | $V_{GS} = -10 \text{ V}, I_D = -2.2 \text{ A}$ | | 0.107 | 0.133 | Ω | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = - 4.5 V, I _D = - 1.6 A | | 0.194 | 0.245 | 2.2 | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 5 V, I _D = - 2.2 A | | 4 | | S | |
| Diode Forward Voltage ^a | V _{SD} | I _S = - 1.05 A, V _{GS} = 0 V | | - 0.82 | - 1.10 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Q_g | | | 3.1 | 5 | | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -2.2 \text{ A}$ | | 1.0 | | nC | |
| Gate-Drain Charge | Q _{gd} | | | 1.6 | | 1 | |
| Turn-On Delay Time | t _{d(on)} | | | 10 | 15 | | |
| Rise Time | t _r | $V_{DD} = -15 \text{ V}, R_{L} = 15 \Omega$ | | 16 | 25 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω | | 17 | 25 | ns | |
| Fall Time | t _f | | | 12 | 20 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = - 1.05 A, dI/dt = 100 A/μs | | 18 | 30 | | |

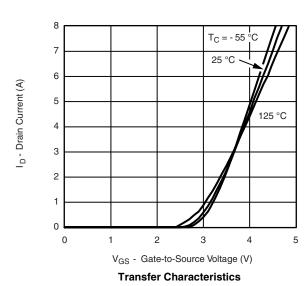
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



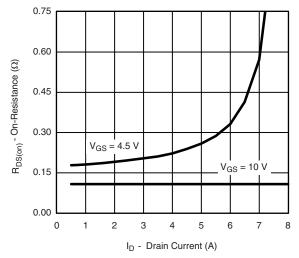




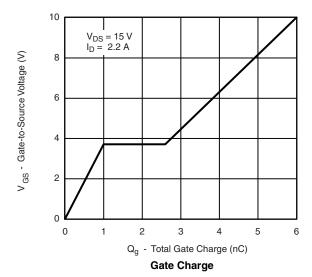


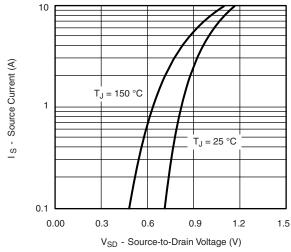


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

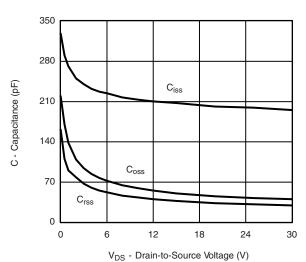


On-Resistance vs. Drain Current

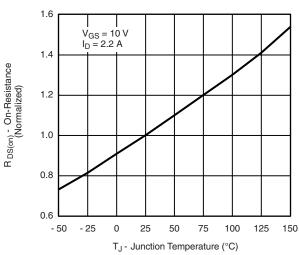




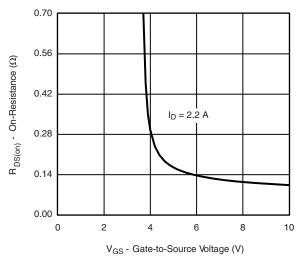
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature

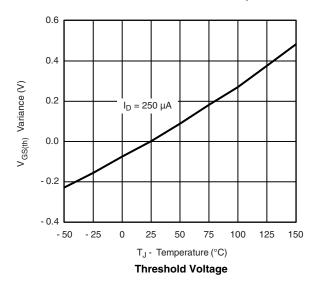


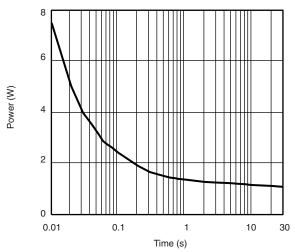
On-Resistance vs. Gate-to-Source Voltage

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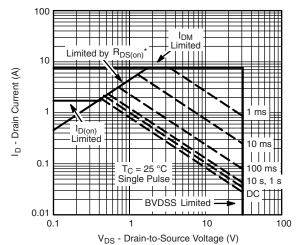
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



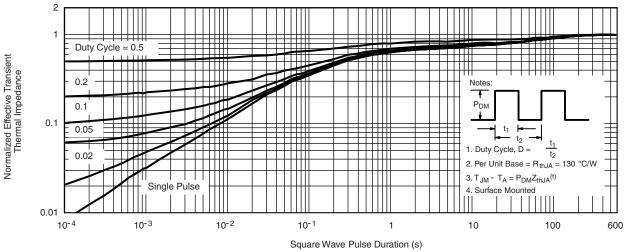


Single Pulse Power, Junction-to-Ambient



* $V_{GS} > \mbox{minimum } V_{GS}$ at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

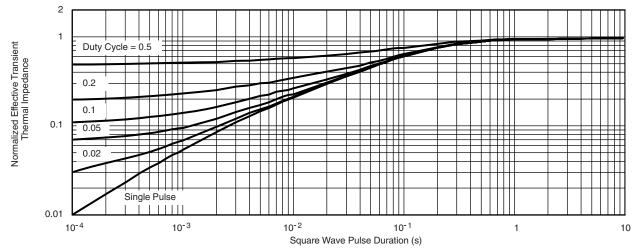


Normalized Thermal Transient Impedance, Junction-to-Ambient





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

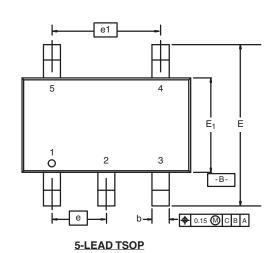
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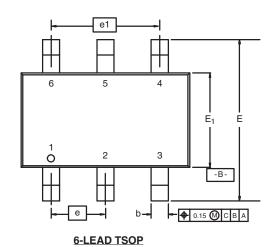


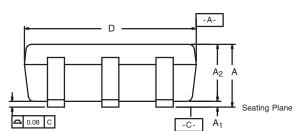


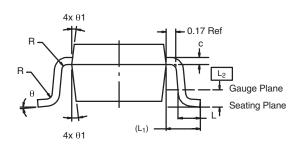
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C









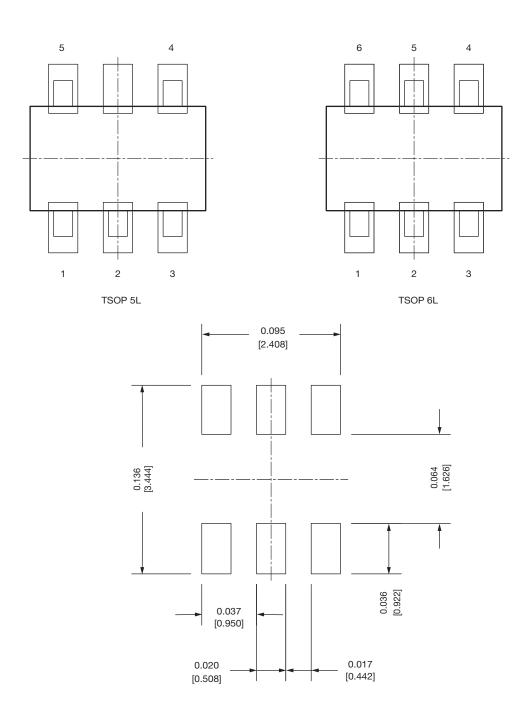
| | MILLIMETERS | | | ı | NCHES | | |
|---|---------------|----------|------|-----------------|-------|-------|--|
| Dim | Min | Nom | Max | Min | Nom | Max | |
| Α | 0.91 | - | 1.10 | 0.036 | - | 0.043 | |
| A ₁ | 0.01 | - | 0.10 | 0.0004 | - | 0.004 | |
| A ₂ | 0.90 | - | 1.00 | 0.035 | 0.038 | 0.039 | |
| b | 0.30 | 0.32 | 0.45 | 0.012 | 0.013 | 0.018 | |
| С | 0.10 | 0.15 | 0.20 | 0.004 0.006 | | 0.008 | |
| D | 2.95 | 3.05 | 3.10 | 0.116 0.120 | | 0.122 | |
| Е | 2.70 | 2.85 | 2.98 | 0.106 | 0.112 | 0.117 | |
| E ₁ | 1.55 | 1.65 | 1.70 | 0.061 | 0.065 | 0.067 | |
| е | | 0.95 BSC | | 0.0374 BSC | | | |
| e ₁ | 1.80 | 1.90 | 2.00 | 0.071 0.075 0.0 | | | |
| L | 0.32 | - | 0.50 | 0.012 | - | 0.020 | |
| L ₁ | 0.60 Ref | | | 0.024 Ref | | | |
| L ₂ | 0.25 BSC | | | 0.010 BSC | | | |
| R | 0.10 | - | - | 0.004 | - | - | |
| θ | 0° | 4° | 8° | 0° | 4° | 8° | |
| θ_1 | 7° Nom 7° Nom | | | | | | |
| ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540 | | | | | | | |

Document Number: 71200 18-Dec-06

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Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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